

Specification of Multi-crystalline 156 mm silicon wafer

Conductivity type	P-type
Dopant	Boron
Dimension	156±0.5mm
Thickness	200±20μm
Lifetime	≥2μs
Resistivity	1.0~3.0Ω*cm 3.0~6.0Ω*cm
Oxygen concentration	< 1X10 ¹⁸ atoms/cm ³
Carbon concentration	< 8×10 ¹⁶ atoms/cm ³
RRV	<15%
TTV	≤35μm
Diagonal A、B(bevel)	A:219.9~221.3mm; B:219.5±0.5mm
Bevel edge width	0.5~2mm
Saw marks(steps)	depth≤15μm
Edge defect	Length≤0.5mm, Depth≤0.3mm, Each slice of edge defect not more than 2
Warp	≤75μm
Surface	As cut and cleaned, No visual cracks , pin hole, stains.